

FEATURES

- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)



Device Marking and Package Information		
Device	Package	Marking
IRFP460PBF	TO-247	IRFP460

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted			
Parameter	Symbol	Value	Unit
		TO-247	
Drain-Source Voltage ($V_{GS} = 0\text{V}$)	V_{DS}	500	V
Continuous Drain Current	I_D	18	A
Pulsed Drain Current (note1)	I_{DM}	72	A
Gate-Source Voltage	V_{GS}	± 30	V
Single Pulse Avalanche Energy (note2)	E_{AS}	980	mJ
Avalanche Current (note1)	I_{AS}	14	A
Repetitive Avalanche Energy (note1)	E_{AR}	588	mJ
Power Dissipation ($T_C = 25^\circ\text{C}$)	P_D	160	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150	$^\circ\text{C}$

Thermal Resistance			
Parameter	Symbol	Value	Unit
		TO-247	
Thermal Resistance, Junction-to-Case	R_{thJC}	0.6	K/W
Thermal Resistance, Junction-to-Ambient	R_{thJA}	40	

Specifications T _J = 25°C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	500	--	--	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 500V, V _{GS} = 0V, T _J = 25°C	--	--	1	μA
Gate-Source Leakage	I _{GSS}	V _{GS} = ±30V	--	--	±100	nA
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	3.0	--	4.0	V
Drain-Source On-Resistance (Note3)	R _{DS(on)}	V _{GS} = 10V, I _D = 9A	--	0.28	0.34	Ω
Dynamic						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 25V, f = 1.0MHz	--	2367	--	pF
Output Capacitance	C _{oss}		--	228	--	
Reverse Transfer Capacitance	C _{rss}		--	15	--	
Total Gate Charge	Q _g	V _{DD} =400V, I _D = 18A, V _{GS} = 10V	--	53.4	--	nC
Gate-Source Charge	Q _{gs}		--	10	--	
Gate-Drain Charge	Q _{gd}		--	20	--	
Turn-on Delay Time	t _{d(on)}	V _{DD} = 250V, I _D =18A, R _G = 25 Ω	--	51.3	--	ns
Turn-on Rise Time	t _r		--	36.5	--	
Turn-off Delay Time	t _{d(off)}		--	232	--	
Turn-off Fall Time	t _f		--	61	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I _S	T _C = 25 °C	--	--	18	A
Pulsed Diode Forward Current	I _{SM}		--	--	72	
Body Diode Voltage	V _{SD}	T _J = 25°C, I _{SD} = 9A, V _{GS} = 0V	--	--	1.4	V
Reverse Recovery Time	t _{rr}	V _{GS} = 0V, I _S = 18A, di _F /dt =100A /μs	--	497	--	ns
Reverse Recovery Charge	Q _{rr}		--	4	--	μC

Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $L=10mH, V_{DD} = 50V, R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
3. Pulse Test: Pulse width $\leq 300\mu s$, Duty Cycle $\leq 1\%$

Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics ($T_J = 25^\circ\text{C}$)

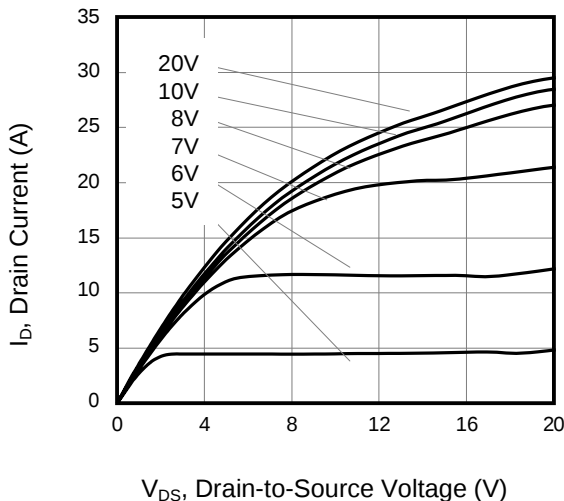


Figure 2. Body Diode Forward Voltage

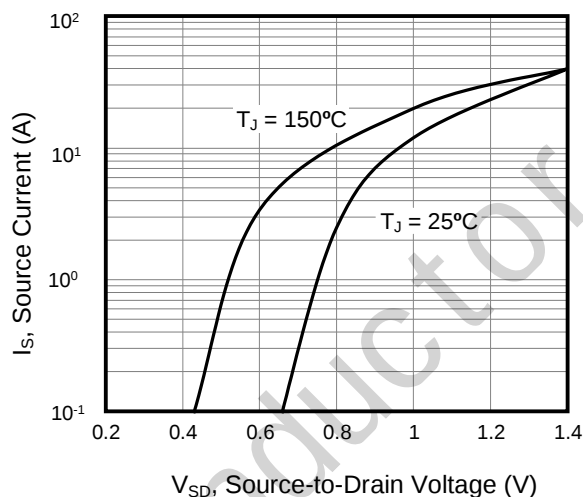


Figure 3. Drain Current vs. Temperature

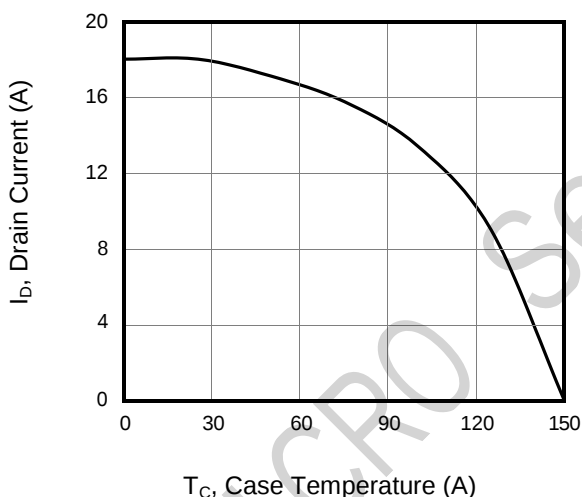


Figure 4. BV_{DSS} Variation vs. Temperature

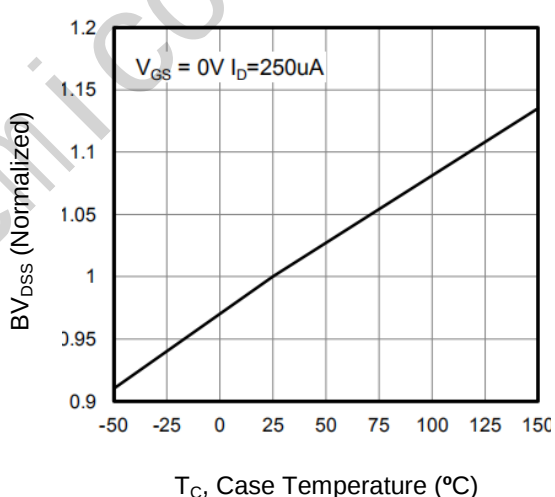


Figure 5. Transfer Characteristics

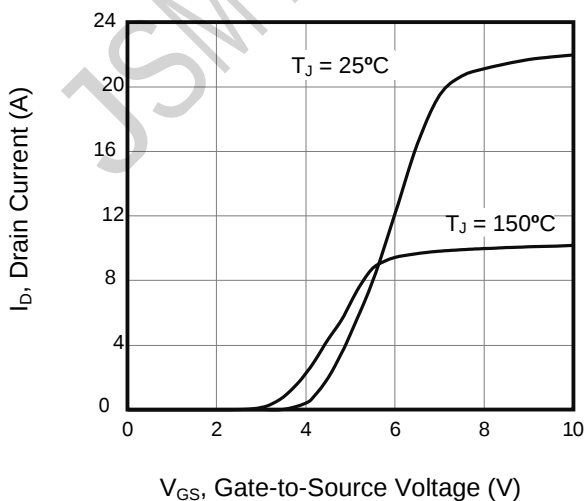
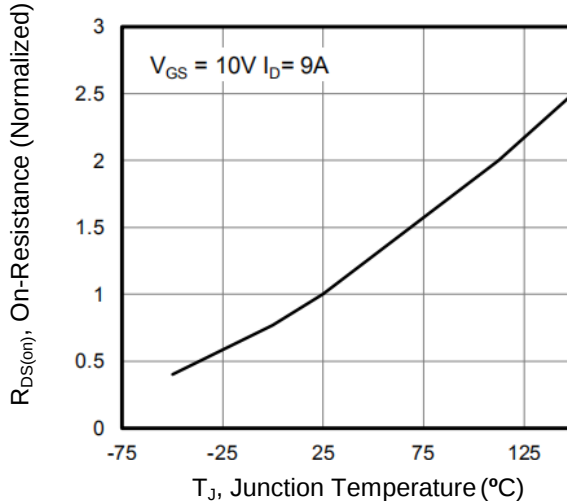


Figure 6. On-Resistance vs. Temperature



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. Capacitance

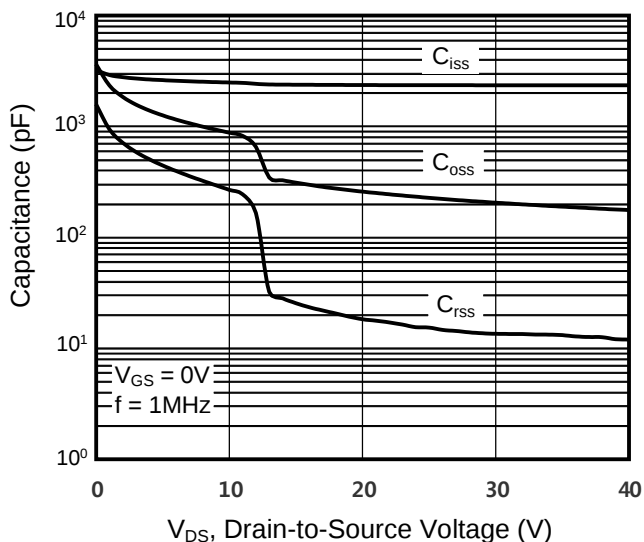


Figure 8. Gate Charge

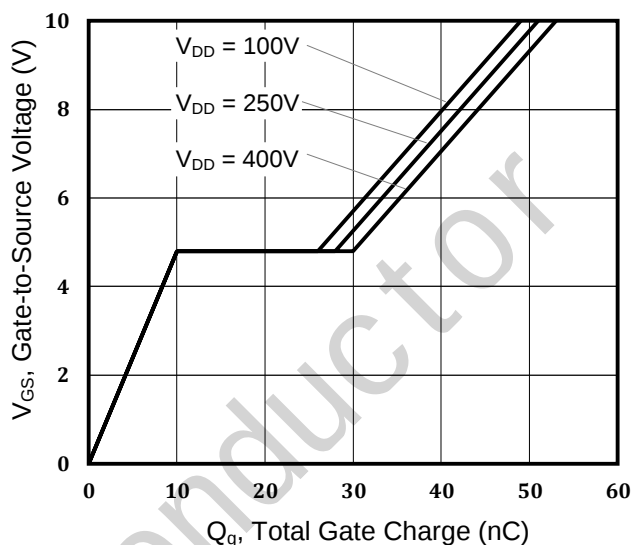


Figure 9. Transient Thermal Impedance
TO-220F

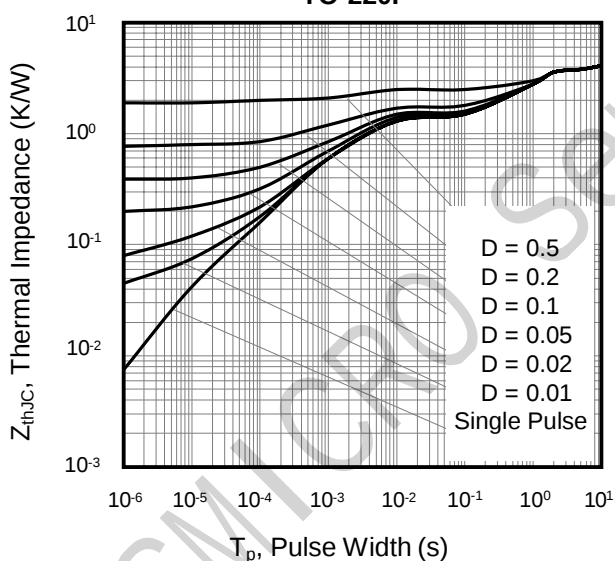


Figure 10. Transient Thermal Impedance
TO-220, TO-3P

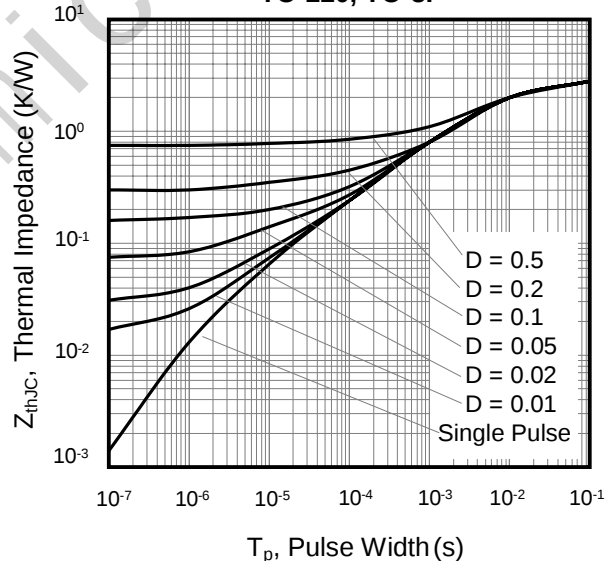


Figure A: Gate Charge Test Circuit and Waveform

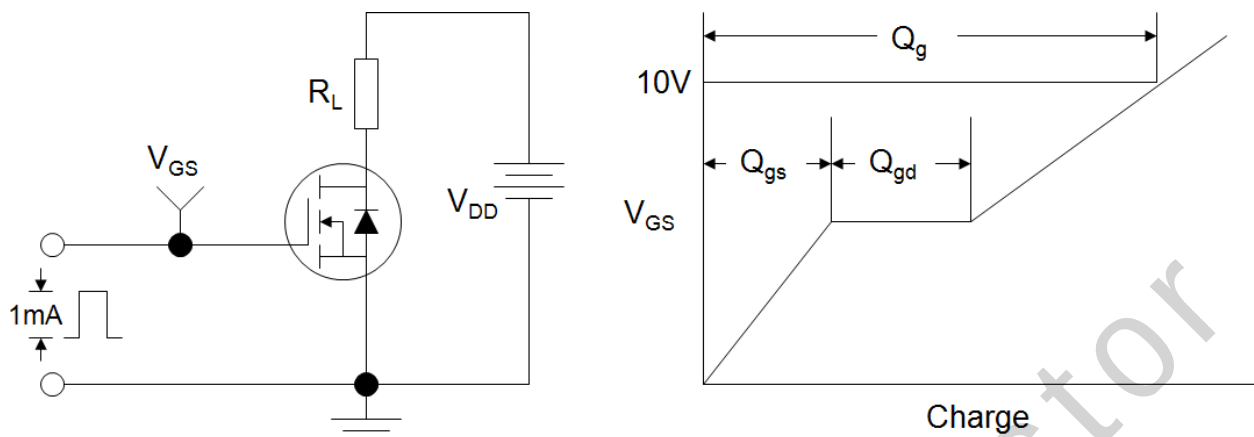


Figure B: Resistive Switching Test Circuit and Waveform

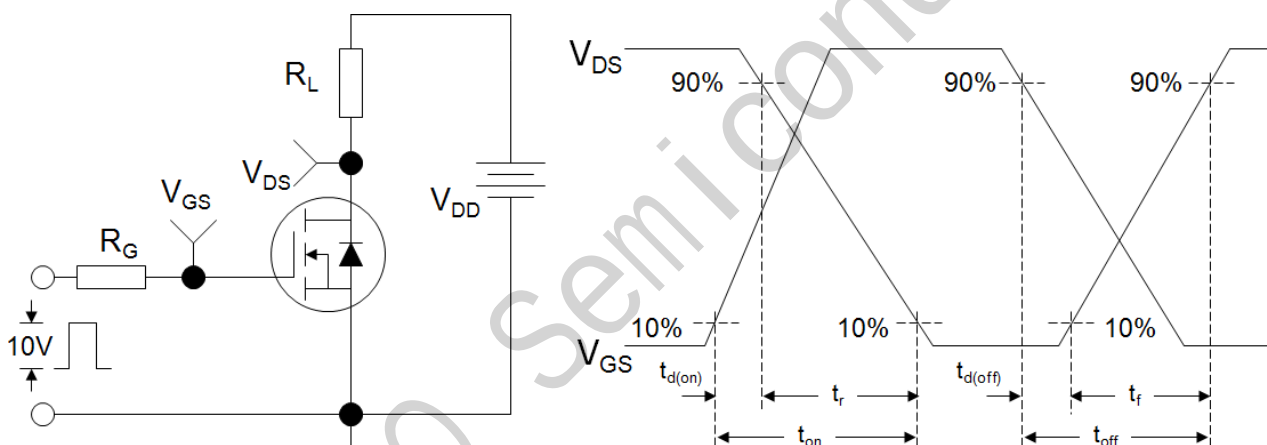
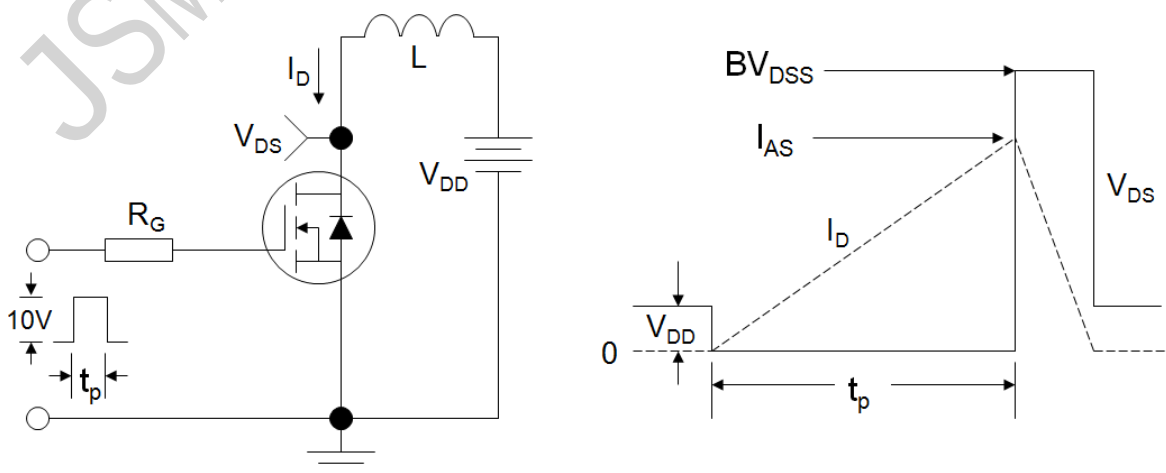
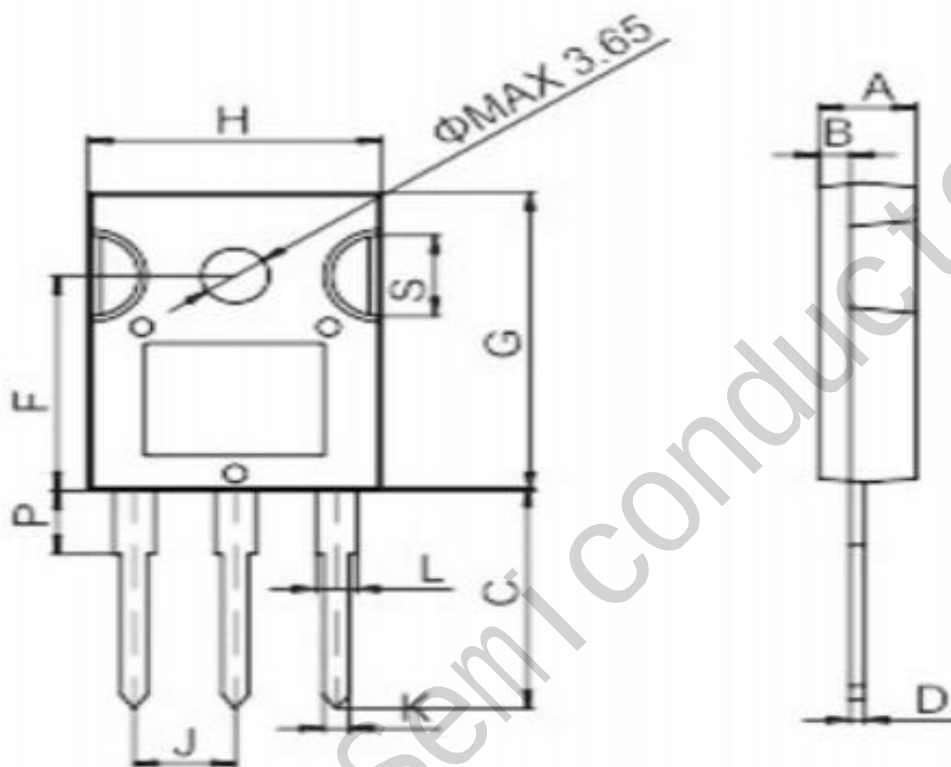


Figure C: Unclamped Inductive Switching Test Circuit and Waveform



TO-247



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.9		5.4	0.193		0.213
B	1.6		2.0	0.063		0.079
C	14.35		15.4	0.565		0.606
D	0.5		0.8	0.020		0.031
F	14.4		15.1	0.567		0.594
G	19.7		20.6	0.775		0.811
H	15.4		16.2	0.606		0.638
J	5.3		5.6	0.209		0.220
K	1.3		1.5	0.051		0.059
L	2.8		3.3	0.110		0.130
P	3.7		4.2	0.146		0.165
S	5.35		5.65	0.211		0.222